

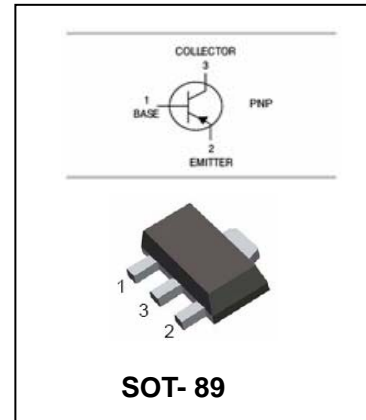


PNP medium power Transistor

BC869

FEATURES

- Low voltage.
- High current.



APPLICATIONS

- Low voltage,high current LF applications.
- Complement to BC868.

ORDERING INFORMATION

Type No.	Marking	Package Code
BC869	CEC/CGC/CHC	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-32	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	DC Collector Current	-1	A
I_{CM}	Peak Collector Current	-2	A
I_{BM}	Peak base current	-200	mA
P_{tot}	Total power dissipation $T_{amb} \leq 25^\circ C$	1.35	W
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	°C



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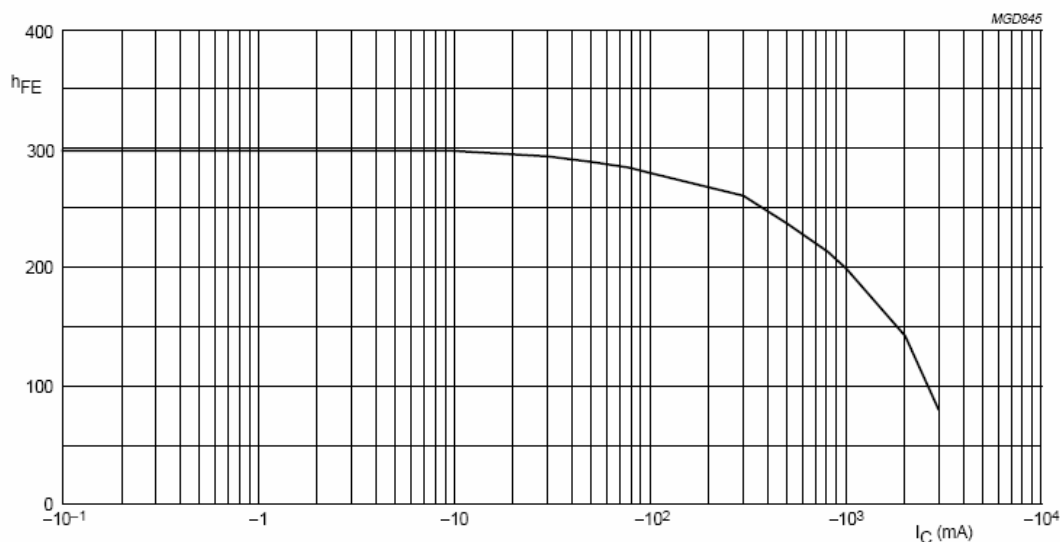
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector cut-off current	I _{CBO}	V _{CB} =-25V I _E =0		-100	nA
		V _{CB} =-25V I _E =0, T _j =150°C		-10	μA
Emmitter cut-off current	I _{EBO}	V _{CE} =-5V I _C =0		-100	nA
DC current gain	h _{FE}	V _{CE} =-10V I _C =-5mA	50		
		V _{CE} =-1V I _C =-500mA			
		BC869	100	375	
		BC869-16	100	160	
		BC869-25	160	375	
		V _{CE} =-1V I _C =-1A	60		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A I _B =-100mA		-0.5	V
Base-emitter voltage	V _{BE}	I _C =-1A, V _{CE} =-1V		-1	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz	40		MHz

CLASSIFICATION H_{FE}

Range	100-375	100-250	160-375
Marking	CEC	CGC	CHC

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



V_{CE} = -1 V.

Fig 1 DC current gain; typical values.

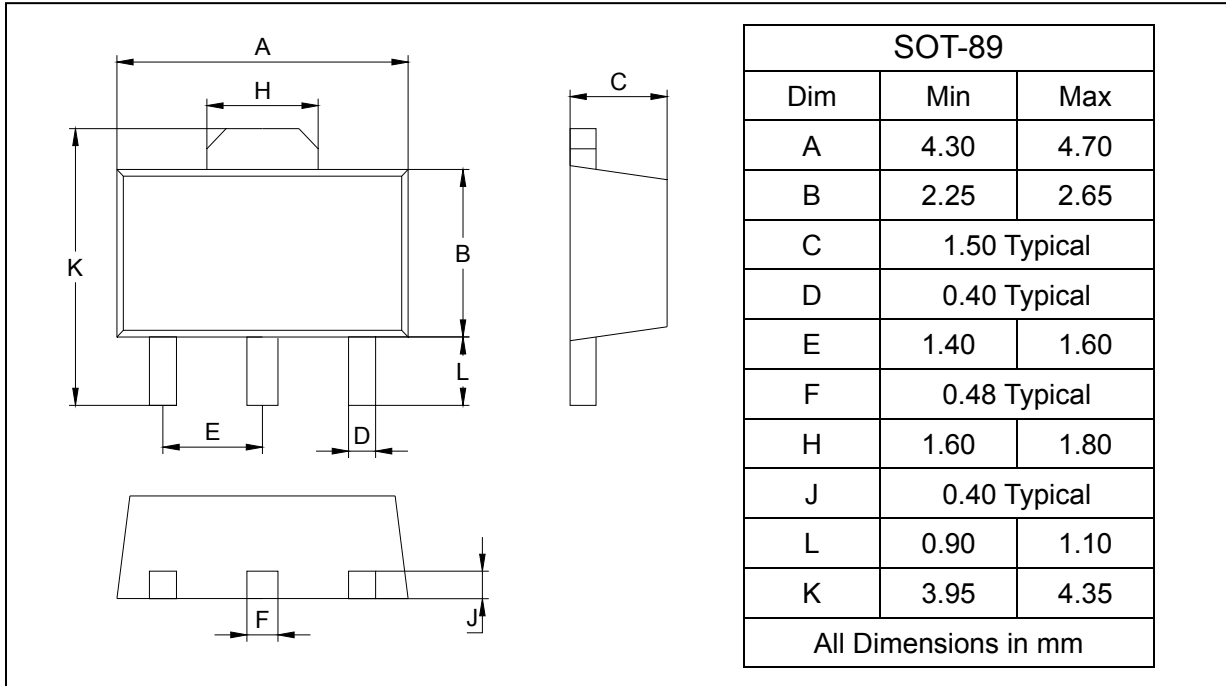
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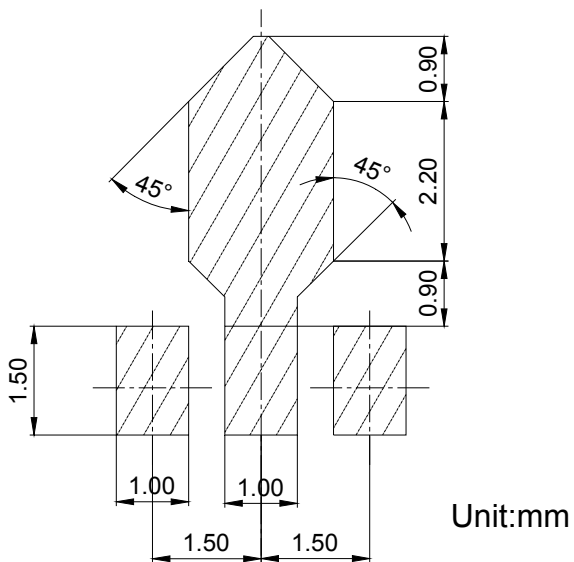
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BC869	SOT-89	1000/Tape&Reel